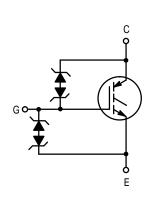
Product Preview Internally Clamped N-Channel IGBT

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features Gate–Emitter ESD protection, Gate Collector Over– Voltage Protection from monolithic circuitry for usage as an Ignition Coil Driver.

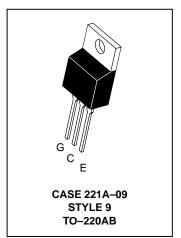
- Temperature Compensated Gate Collector Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage to Interface Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability





MGP15N43CL

N-CHANNEL IGBT VCE(on) = 1.8 V 430 VOLTS CLAMPED



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	CLAMPED	Vdc
Collector–Gate Voltage	VCER	CLAMPED	Vdc
Gate-Emitter Voltage	VGE	CLAMPED	Vdc
Collector Current — Continuous	IC	15	Adc
Total Power Dissipation Derate above 25°C	PD	136 0.91	Watts W/°C
Operating and Storage Temperature Range	TJ, Tstg	-55 to 175	°C
UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS (T $_{\rm J}$ < 150)°C)		
Single Pulse Collector–to–Emitter Avalanche Energy $V_{CC} = 50 \text{ V}, \text{ V}_{GE} = 5.0 \text{ V}, \text{ PEAK I}_{L} = 14.2 \text{ A}, \text{ L} = 3.0 \text{ mH}, \text{ Starting T}_{J} = 25^{\circ}\text{C}$ $V_{CC} = 50 \text{ V}, \text{ V}_{GE} = 5.0 \text{ V}, \text{ PEAK I}_{L} = 10 \text{ A}, \text{ L} = 3.0 \text{ mH}, \text{ Starting T}_{J} = 150^{\circ}\text{C}$	EAS	300 150	mJ
THERMAL CHARACTERISTICS	-		
Thermal Resistance — Junction-to-Case — Junction-to-Ambient	R _θ JC R _θ JA	1.1 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	TL	260	°C

This document contains information on a new product. Specifications and information herein are subject to change without notice.



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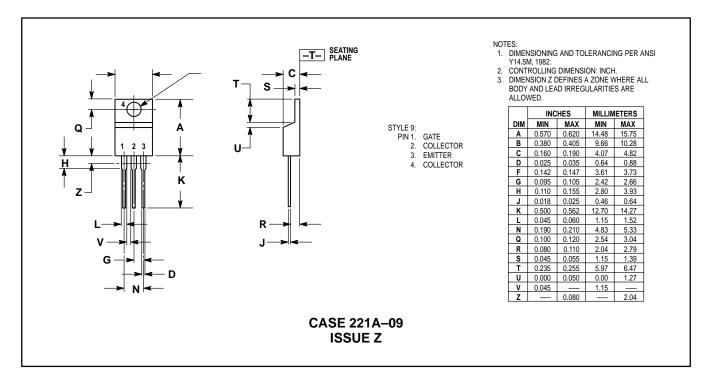
ELECTRICAL CHARACTERISTICS (T_J = 25° C unless otherwise noted)

Cha	racteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			•	
Collector–Emitter Clamp Voltage $(I_C = 1.0 \text{ mA}, T_J = -40^{\circ}\text{C} \text{ to } 175^{\circ}$	C)	V _(BR) CES	_	430	_	Vdc
Zero Gate Voltage Collector Current (V _{CE} = 360 V, V _{GE} = 0 V) (V _{CE} = 360 V, V _{GE} = 0 V, T _J = 15		ICES			10 150	μAdc
Gate–Emitter Clamp Voltage (I _G = 5.0 mA)		V _(BR) GES	17	_	22	Vdc
Gate–Emitter Leakage Current (V _{GE} = 10 V)		IGES	_	_	10	μAdc
ON CHARACTERISTICS (1)		•				
Gate Threshold Voltage (V _{GE} = V _{CE} , I _C = 1.0 mA) Threshold Temperature Coefficier	nt (Negative)	VGE(th)	1.3	1.8 4.4	2.1	Vdc mV/°C
Collector-to-Emitter On-Voltage ($V_{GE} = 3.5 \text{ V}, I_C = 6.0 \text{ A}$) ($V_{GE} = 4.0 \text{ V}, I_C = 10 \text{ A}, T_J = 150 \text{ A}$)°C)	VCE(on)			2.0 1.8	Volts
Forward Transconductance ($V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ A}$)		9fe	8.0	20	_	Mhos
DYNAMIC CHARACTERISTICS						
Input Capacitance	(V _{CC} = 15 V, V _{GE} = 0 V, f = 1.0 MHz)	Cies	—	TBD	-	pF
Output Capacitance		C _{oes}	—	TBD	-	
Transfer Capacitance		C _{res}	—	TBD	—	
SWITCHING CHARACTERISTICS (1)	•				
Turn–Off Delay Time	$(V_{CC} = 400 \text{ V}, \text{ I}_{C} = 6.5 \text{ A}, R_{G} = 1.0 \text{ k}\Omega, L = 300 \mu\text{H})$	^t d(off)	—	TBD	—	μSec
Fall Time		t _f	—	TBD	—	1
Turn–On Delay Time	$(V_{CC} = 10 V, I_C = 6.5 A, R_G = 1.0 k\Omega, R_L = 1.0 Ω)$	^t d(on)	—	TBD	—	μSec
Rise Time		tr	—	TBD	-	1
Gate Charge	(V _{CC} = 350 V, I _C = 15 A, V _{GE} = 5.0 V)	QT	—	TBD	- 1	nC
		Q ₁	—	TBD	-	1
		Q ₂	—	TBD	_	1

(1) Pulse Test: Pulse Width \leq 300 μ S, Duty Cycle \leq 2%.

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PACKAGE DIMENSIONS



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